

## **Description**

The SFT1342 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

#### **General Features**

V<sub>DS</sub> =- 60V, I<sub>D</sub> =-30A

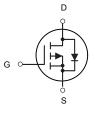
 $R_{DS(ON)}$  < 33m $\Omega$  @  $V_{GS}$ =-10V

## **Application**

PWM applications

Load switch

Power management



P-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
SFT1342	TO-252-2L	HXY MOSFET	2500

#### ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage (Vcs=0V)	-60	V
V <sub>GS</sub>	Gate-Source Voltage (V <sub>DS</sub> =0V)	V	
1-	Drain Current-Continuous(Tc=25℃)	-30	А
l <sub>D</sub>	Drain Current-Continuous(Tc=100°C)	-25.5	А
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-144	А
D-	Maximum Power Dissipation(T <sub>C</sub> =25 ℃)	79	W
P <sub>D</sub>	Maximum Power Dissipation(T <sub>C</sub> =100℃)	39.5	W
Eas	Avalanche energy (Note 2)	196	mJ
TJ, TSTG	Operating Junction and Storage Temperature Range	-55 To 175	${\mathbb C}$



### Electrical Characteristics (T<sub>J</sub>=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μΑ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V		±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-1.8	-2.5	V
<b>g</b> FS	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-15A		35		S
	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		29	33	mΩ
Rds(on)		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A		35	46	mΩ
Ciss	Input Capacitance			4026		pF
Coss	Output Capacitance	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1.0MHz		134		pF
Crss	Reverse Transfer Capacitance			98		pF
t <sub>d(on)</sub>	Turn-on Delay Time			12.2		nS
tr	Turn-on Rise Time	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V,		10		nS
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_L=1.5\Omega$ , $R_{GEN}=3\Omega$		64		nS
t <sub>f</sub>	Turn-Off Fall Time			14		nS
Qg	Total Gate Charge			68		nC
Qgs	Gate-Source Charge	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V, I <sub>D</sub> =-20A		10.5		nC
$Q_{gd}$	Gate-Drain Charge			13		nC
Isp	Source-Drain Current (Body Diode)				30	Α
Vsp	Forward on Voltage (Note 3)	V <sub>G</sub> s=0V, Is=-15A			-1.2	V
<b>t</b> rr	Reverse Recovery Time	I <sub>F</sub> =-20A, di/dt=100A/μs		26		ns
Qrr	Reverse Recovery Charge	I <sub>F</sub> =-20A, di/dt=100A/μs		29		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature. Notes 2.E<sub>AS</sub> condition:  $T_J$ =25°C, $V_{DD}$ =40V, $V_{G}$ =-10V, Rg=25 $\Omega$ , L=0.5mH. Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



# **Typical Electrical And Thermal Characteristics (Curves)**

Figure 1. Output Characteristics

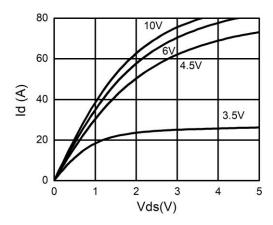


Figure 2. Transfer Characteristics

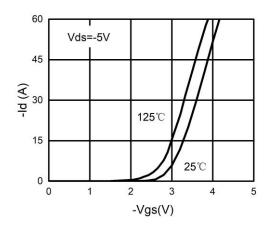


Figure 3. Power Dissipation

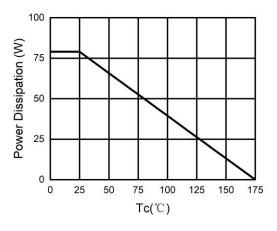


Figure 4. Drain Current

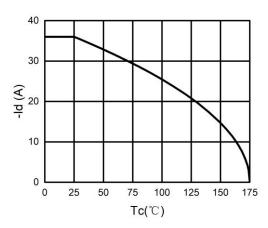


Figure 5. BV<sub>DSS</sub> vs Junction Temperature

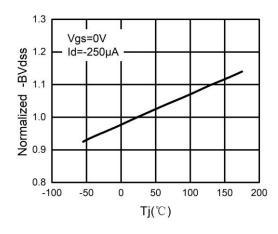


Figure 6. R<sub>DS(ON)</sub> vs Junction Temperature

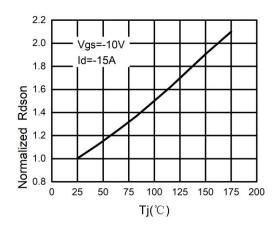




Figure 7. Gate Charge Waveforms

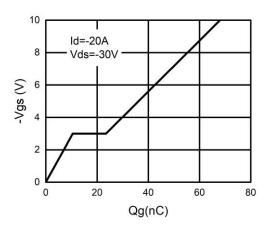


Figure 8. Capacitance

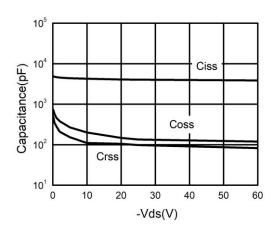


Figure 9. Body-Diode Characteristics

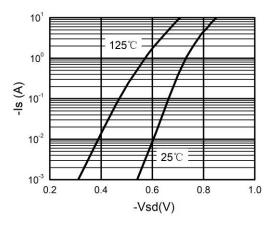
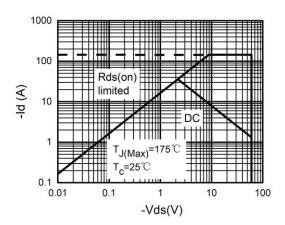
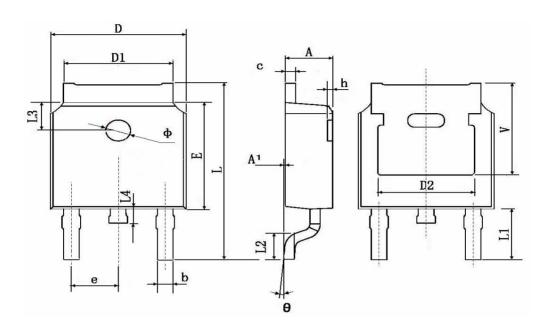


Figure 10. Maximum Safe Operating Area





# **TO-252-2L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		

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